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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

XF

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	15
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 6x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-WFQFN Exposed Pad
Supplier Device Package	24-HWQFN (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f1007cana-w0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

Dia	Destaurs	Data flash		(3/12)
Pin count	Package	Data flash	Fields of Application	Ordering Part Number
36 pins	36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)	Mounted	A	R5F100CAALA#U0, R5F100CCALA#U0, R5F100CDALA#U0, R5F100CEALA#U0, R5F100CFALA#U0, R5F100CGALA#U0 R5F100CAALA#W0, R5F100CCALA#W0, R5F100CDALA#W0, R5F100CEALA#W0, R5F100CFALA#W0, R5F100CGALA#W0
			G	R5F100CAGLA#U0, R5F100CCGLA#U0, R5F100CDGLA#U0, R5F100CEGLA#U0, R5F100CFGLA#U0, R5F100CGGLA#U0 R5F100CAGLA#W0, R5F100CCGLA#W0, R5F100CDGLA#W0, R5F100CEGLA#W0, R5F100CFGLA#W0, R5F100CGGLA#W0
		Not mounted	A	R5F101CAALA#U0, R5F101CCALA#U0, R5F101CDALA#U0, R5F101CEALA#U0, R5F101CFALA#U0, R5F101CGALA#U0 R5F101CAALA#W0, R5F101CCALA#W0, R5F101CDALA#W0, R5F101CEALA#W0, R5F101CFALA#W0, R5F101CGALA#W0
40 pins	40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)	Mounted	A	R5F100EAANA#U0, R5F100ECANA#U0, R5F100EDANA#U0, R5F100EEANA#U0, R5F100EFANA#U0, R5F100EGANA#U0, R5F100EHANA#U0 R5F100EAANA#W0, R5F100ECANA#W0, R5F100EDANA#W0, R5F100EEANA#W0, R5F100EFANA#W0, R5F100EGANA#W0, R5F100EHANA#W0
			D	R5F100EADNA#U0, R5F100ECDNA#U0, R5F100EDDNA#U0, R5F100EEDNA#U0, R5F100EFDNA#U0, R5F100EGDNA#U0, R5F100EHDNA#U0 R5F100EADNA#W0, R5F100ECDNA#W0, R5F100EDDNA#W0, R5F100EEDNA#W0, R5F100EFDNA#W0, R5F100EGDNA#W0, R5F100EHDNA#W0
			G	R5F100EAGNA#U0, R5F100ECGNA#U0, R5F100EDGNA#U0, R5F100EEGNA#U0, R5F100EFGNA#U0, R5F100EGGNA#U0, R5F100EHGNA#U0 R5F100EAGNA#W0, R5F100ECGNA#W0, R5F100EDGNA#W0, R5F100EEGNA#W0, R5F100EFGNA#W0, R5F100EGGNA#W0, R5F100EHGNA#W0
		Not mounted	A	R5F101EAANA#U0, R5F101ECANA#U0, R5F101EDANA#U0, R5F101EEANA#U0, R5F101EFANA#U0, R5F101EGANA#U0, R5F101EHANA#U0 R5F101EAANA#W0, R5F101ECANA#W0, R5F101EDANA#W0, R5F101EEANA#W0, R5F101EFANA#W0, R5F101EGANA#W0, R5F101EHANA#W0
			D	R5F101EADNA#U0, R5F101ECDNA#U0, R5F101EDDNA#U0, R5F101EEDNA#U0, R5F101EFDNA#U0, R5F101EGDNA#U0, R5F101EHDNA#U0 R5F101EADNA#W0, R5F101ECDNA#W0, R5F101EDDNA#W0, R5F101EEDNA#W0, R5F101EFDNA#W0, R5F101EGDNA#W0, R5F101EHDNA#W0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5 mm pitch)



	А	В	С	D	E	F	_
	P60/SCLA0	Vdd	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	
6							6
	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	
5							5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/TI00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AVrefp	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/TI02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	А	В	С	D	E	F	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



1.4 Pin Identification

ANI0 to ANI14,		REGC:	Regulator capacitance
ANI16 to ANI26:	Analog input	RESET:	Reset
AVREFM:	A/D converter reference	RTC1HZ:	Real-time clock correction clock
	potential (– side) input		(1 Hz) output
AVREFP:	A/D converter reference	RxD0 to RxD3:	Receive data
	potential (+ side) input	SCK00, SCK01, SCK10,	
EVDD0, EVDD1:	Power supply for port	SCK11, SCK20, SCK21,	
EVsso, EVss1:	Ground for port	SCLA0, SCLA1:	Serial clock input/output
EXCLK:	External clock input (Main	SCLA0, SCLA1, SCL00,	
	system clock)	SCL01, SCL10, SCL11,	
EXCLKS:	External clock input	SCL20,SCL21, SCL30,	
	(Subsystem clock)	SCL31:	Serial clock output
INTP0 to INTP11:	Interrupt request from	SDAA0, SDAA1, SDA00,	
	peripheral	SDA01,SDA10, SDA11,	
KR0 to KR7:	Key return	SDA20,SDA21, SDA30,	
P00 to P07:	Port 0	SDA31:	Serial data input/output
P10 to P17:	Port 1	SI00, SI01, SI10, SI11,	
P20 to P27:	Port 2	SI20, SI21, SI30, SI31:	Serial data input
P30 to P37:	Port 3	SO00, SO01, SO10,	
P40 to P47:	Port 4	SO11, SO20, SO21,	
P50 to P57:	Port 5	SO30, SO31:	Serial data output
P60 to P67:	Port 6	TI00 to TI07,	
P70 to P77:	Port 7	TI10 to TI17:	Timer input
P80 to P87:	Port 8	TO00 to TO07,	
P90 to P97:	Port 9	TO10 to TO17:	Timer output
P100 to P106:	Port 10	TOOL0:	Data input/output for tool
P110 to P117:	Port 11	TOOLRxD, TOOLTxD:	Data input/output for external device
P120 to P127:	Port 12	TxD0 to TxD3:	Transmit data
P130, P137:	Port 13	VDD:	Power supply
P140 to P147:	Port 14	Vss:	Ground
P150 to P156:	Port 15	X1, X2:	Crystal oscillator (main system clock)
PCLBUZ0, PCLBUZ1:	Programmable clock	XT1, XT2:	Crystal oscillator (subsystem clock)
	output/buzzer output		



1.5.10 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.



[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

							(1/2)			
	Item	80-	•	100)-pin	128-pin				
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx			
Code flash m	emory (KB)	96 te	o 512	96 t	o 512	192	to 512			
Data flash me	emory (KB)	8	_	8	-	8	-			
RAM (KB)		8 to 3	2 Note 1	8 to 3	32 Note 1	16 to 5	32 Note 1			
Address space	e	1 MB								
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	mic) oscillation, I main) mode: 1 I main) mode: 1 main) mode: 1 e main) mode: 1	to 20 MHz (V_{DD} to 16 MHz (V_{DD} to 8 MHz (V_{DD} =	= 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)				
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	I main) mode: 1 I main) mode: 1 main) mode: 1 e main) mode: 1	to 16 MHz (V _{DD} to 8 MHz (V _{DD} =	= 2.4 to 5.5 V), 1.8 to 5.5 V),					
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	I subsystem cloc	k input (EXCLKS	i)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)								
General-purp	ose register	(8-bit register \times 8) \times 4 banks								
Minimum inst	ruction execution time	0.03125 μ s (High-speed on-chip oscillator: f _H = 32 MHz operation)								
		0.05 µs (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 µs (Subsystem clock: fsue = 32.768 kHz operation)								
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 								
I/O port	Total	7	74		92	1	20			
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand le]: 21)	(N-ch O.D. I/O	82 [EV⊳⊳ withstand ge]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand ge]: 25)			
	CMOS input		5	5			5			
	CMOS output		1		1		1			
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4			
Timer	16-bit timer	12 cha	annels	12 ch	annels	16 ch	annels			
	Watchdog timer	1 cha	annel	1 ch	annel	1 cha	annel			
	Real-time clock (RTC)	1 cha	annel	1 ch	annel	1 cha	annel			
	12-bit interval timer (IT)	1 cha	annel	1 ch	annel	1 cha	annel			
	Timer output	12 channels (PWM outputs:	10 ^{Note 2})	12 channels (PWM outputs:	10 Note 2)	16 channels (PWM outputs: 14 ^{Note 2})				
	RTC output	1 channel • 1 Hz (subsyster)	tem clock: fsub =	32.768 kHz)						

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H

R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library** for RL78 Family (R20UT2944).



Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	-70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	Iol1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operati	on mode	-40 to +85	°C
temperature		In flash memory	programming mode		
Storage temperature	Tstg			-65 to +150	°C

Absolute Maximum Ratings (TA = 25°C) (2/2)

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



- **Notes 1.** Total current flowing into Vbb, EVbbb, and EVbb1, including the input leakage current flowing when the level of the input pin is fixed to Vbb, EVbb0, and EVbb1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 - HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz
 - 2.4 V \leq V_{DD} \leq 5.5 V@1 MHz to 16 MHz
 - LS (low-speed main) mode: $~~1.8~V \leq V_{\text{DD}} \leq 5.5~V~$ @ 1 MHz to 8 MHz
 - LV (low-voltage main) mode: 1.6 V \leq V_{DD} \leq 5.5 V@1 MHz to 4 MHz
 - 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



- 6. Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- 9. Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode.

Remarks 1. fill: Low-speed on-chip oscillator clock frequency

- **2.** fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- 3. fclk: CPU/peripheral hardware clock frequency
- 4. Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



Parameter	Symbol	Conditions	、 U	h-speed Mode	``	/-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\label{eq:constraint} \begin{array}{l} 2.7 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} = 50 \ pF, \ R_{\text{b}} = 2.7 \ k\Omega \end{array}$	1/fмск + 85 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} \leq 5.5 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 3 \ k\Omega \end{split}$	1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		1/fмск + 145 _{Note2}		ns
		$\label{eq:linear} \begin{split} 1.8 \ V &\leq EV_{\text{DD0}} < 2.7 \ V, \\ C_{\text{b}} &= 100 \ p\text{F}, \ R_{\text{b}} = 5 \ k\Omega \end{split}$	1/fмск + 230 _{Note2}		1/f _{MCK} + 230 _{Note2}		1/fмск + 230 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{\tiny DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 \mbox{ k}\Omega \end{array}$	1/fмск + 290 _{Note2}		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	—		1/f _{MCK} + 290 _{Note2}		1/fмск + 290 _{Note2}		ns
Data hold time (transmission)	thd:dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 3 k\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{\tiny b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{\tiny b}} = 5 k\Omega \end{array}$	0	405	0	405	0	405	ns
		$1.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	0	405	0	405	0	405	ns
		$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5 \text{ k}\Omega$	_	_	0	405	0	405	ns

(5)	During communication at same potential (simplified I ² C mode) (2/2)
	$(T_{A} = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Notes 1. The value must also be equal to or less than $f_{MCK}/4$.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)







- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- **3.** fMCK: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
 m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

Parameter	Symbol	Conditions	HS (speed	high-	LS (low	· · ·	•	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tкн2, tкL2	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$	tксү2/2 – 12		tксү2/2 - 50		tксү2/2 - 50		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	tксү2/2 – 18		tксү2/2 - 50		tксү2/2 - 50		ns
		$\label{eq:VDD} \begin{split} 1.8 \ V &\leq E V_{\text{DD0}} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{split}$	tксү2/2 - 50		tксү2/2 - 50		tксү2/2 - 50		ns
SIp setup time (to SCKp↑) ^{Note 3}	tsik2	$\begin{array}{l} 4.0 \; V \leq E V_{DD0} \leq 5.5 \; V, \\ 2.7 \; V \leq V_b \leq 4.0 \; V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 2.7 \ V \leq E V_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{array}$	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
Slp hold time (from SCKp↑) ^{Note 4}	tksi2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 5	tkso2	$\label{eq:V_def} \begin{array}{l} 4.0 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \ 2.7 \ V \leq V_{\text{b}} \leq 4.0 \\ V, \\ C_{\text{b}} = 30 \ pF, \ R_{\text{b}} = 1.4 \ k\Omega \end{array}$		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
		$\label{eq:V_def} \begin{array}{l} 2.7 \; V \leq EV_{\text{DD0}} < 4.0 \; V, \; 2.3 \; V \leq V_{b} \leq 2.7 \\ V, \\ C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{array}$		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$ \begin{split} & 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ & 1.6 \ V \leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ & C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split} $		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

Notes 1. Transfer rate in the SNOOZE mode : MAX. 1 Mbps

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 5. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp[↑]" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number,

n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.



<R>

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

2. The maximum value (MAX.) of the is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$



3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (1/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{∾te 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$2.4~V \leq EV_{DD0} \leq 5.5~V$			-3.0 Note 2	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	$4.0~V \leq EV_{\text{DD0}} \leq 5.5~V$			-30.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-10.0	mA
			$2.4~V \leq EV_{\text{DD0}} < 2.7~V$			-5.0	mA
		Total of P05, P06, P10 to P17, P30, P31, 4 P50 to P57, P64 to P67, P70 to P77, P80 z to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty $\leq 70\%$ ^{Note 3})				-30.0	mA
			$2.7~V \leq EV_{\text{DD0}} < 4.0~V$			-19.0	mA
			$2.4~V \leq EV_{DD0} < 2.7~V$			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{№te 3})	$2.4~V \leq EV_{\text{DD0}} \leq 5.5~V$			-60.0	mA
	Іон2	Per pin for P20 to P27, P150 to P156	2,4 V \leq V_{DD} \leq 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty $\leq 70\%^{Note 3}$)	$2.4~V \leq V_{\text{DD}} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%. The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).
 - Total output current of pins = $(I_{OH} \times 0.7)/(n \times 0.01)$
 - <Example> Where n = 80% and $I_{OH} = -10.0$ mA
 - Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
current, high P30 to P3 P50 to P5 P70 to P7 P90 to P9 P110 to P		P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVDDO				1	μA
	Ілна	P20 to P27, P137, P150 to P156, RESET	$V_{I} = V_{DD}$				1	μA
	Іцнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	1.1.1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVsso				-1	μA
	Ilile	P20 to P27, P137, P150 to P156, RESET	VI = Vss				-1	μA
	Ililis	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = Vss	In input port or external clock input			-1	μA
				In resonator connection			-10	μA
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVsso	, In input port	10	20	100	kΩ

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{ V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (5/5)

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



Parameter	Symbol			MIN.	TYP.	MAX.	Unit		
	DD2	HALT	HS (high- speed main) mode ^{Note 7}	$f_{IH} = 32 \text{ MHz}^{Note 4}$	$V_{DD} = 5.0 V$		0.54	2.90	mA
	Note 2	mode			$V_{DD} = 3.0 V$		0.54	2.90	mA
				$f_{IH} = 24 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.44	2.30	mA
					V _{DD} = 3.0 V		0.44	2.30	mA
				file = 16 MHz ^{Note 4}	$V_{DD} = 5.0 V$		0.40	1.70	mA
					V _{DD} = 3.0 V		0.40	1.70	mA
			HS (high- speed main) mode ^{Note 7}	$f_{MX} = 20 \text{ MHz}^{Note 3}$,	Square wave input		0.28	1.90	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.45	2.00	mA
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.90	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.45	2.00	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 5.0 V$	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{Note 3}$,	Square wave input		0.19	1.02	mA
				$V_{DD} = 3.0 V$	Resonator connection		0.26	1.10	mA
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μA
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.44	0.76	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μA
				$T_A = +25^{\circ}C$	Resonator connection		0.49	0.76	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μA
				$T_A = +50^{\circ}C$	Resonator connection		0.56	1.36	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μA
				$T_A = +70^{\circ}C$	Resonator connection		0.72	2.16	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μA
				$T_A = +85^{\circ}C$	Resonator connection		1.01	3.56	μA
				fsuв = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	μA
				$T_A = +105^{\circ}C$	Resonator connection		3.20	15.56	μA
	IDD3 ^{Note 6}	STOP mode ^{Note 8}	$T_{\text{A}} = -40^{\circ}C$				0.18	0.50	μA
			$T_A = +25^{\circ}C$				0.23	0.50	μA
			$T_A = +50^{\circ}C$				0.30	1.10	μA
			T _A = +70°C				0.46	1.90	μA
			T _A = +85°C				0.75	3.30	μA
			T _A = +105°C	T _A = +105°C			2.94	15.30	μA

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to $+105^{\circ}$ C, 2.4 V $\leq EV_{DD0} \leq V_{DD} \leq 5.5$ V, Vss = EVss₀ = 0 V) (2/2)

(Notes and Remarks are listed on the next page.)



- **Notes 1.** Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVSSD, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V \leq V_DD \leq 5.5 V@1 MHz to 32 MHz 2.4 V \leq V_DD \leq 5.5 V@1 MHz to 16 MHz

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- **Remarks 1.** fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. file: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2) ($T_A = -40$ to $+105^{\circ}C$, 2.4 V $\leq EV_{DD0} = EV_{DD1} \leq V_{DD} \leq 5.5$ V. Vss = $EV_{SS0} = EV_{SS1} = 0$ V)

Parameter	Symbol	Conditions			HS (high-s M	Unit	
					MIN.	MAX.	
Transfer rate	Reception	Reception	$4.0 V \leq EV_{\text{DD0}} \leq 5.5$			fмск/12 ^{Note 1}	bps
			V, $2.7 \text{ V} \leq V_b \leq 4.0 \text{ V}$	Theoretical value of the maximum transfer rate fcLK = 32 MHz, fMCK = fcLK		2.6	Mbps
			$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			fмск/12 ^{Note 1}	bps
				maximum transfer rate		2.6	Mbps
			$2.4 V \le EV_{DD0} < 3.3 V,$			fмск/12 Notes 1,2	bps
			$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate fcLk = 32 MHz, fMck = fcLk		2.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. The following conditions are required for low voltage interface when E_{VDD0} < $V_{DD}.$ 2.4 V \leq EV_{DD0} < 2.7 V : MAX. 1.3 Mbps
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** $V_{b}[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.



3.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.





NOTES FOR CMOS DEVICES

- (1) VOLTAGE APPLICATION WAVEFORM AT INPUT PIN: Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between VIL (MAX) and VIH (MIN) due to noise, etc., the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between VIL (MAX) and VIH (MIN).
- (2) HANDLING OF UNUSED INPUT PINS: Unconnected CMOS device inputs can be cause of malfunction. If an input pin is unconnected, it is possible that an internal input level may be generated due to noise, etc., causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND via a resistor if there is a possibility that it will be an output pin. All handling related to unused pins must be judged separately for each device and according to related specifications governing the device.
- (3) PRECAUTION AGAINST ESD: A strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it when it has occurred. Environmental control must be adequate. When it is dry, a humidifier should be used. It is recommended to avoid using insulators that easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors should be grounded. The operator should be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with mounted semiconductor devices.
- (4) STATUS BEFORE INITIALIZATION: Power-on does not necessarily define the initial status of a MOS device. Immediately after the power source is turned ON, devices with reset functions have not yet been initialized. Hence, power-on does not guarantee output pin levels, I/O settings or contents of registers. A device is not initialized until the reset signal is received. A reset operation must be executed immediately after power-on for devices with reset functions.
- (5) POWER ON/OFF SEQUENCE: In the case of a device that uses different power supplies for the internal operation and external interface, as a rule, switch on the external power supply after switching on the internal power supply. When switching the power supply off, as a rule, switch off the external power supply and then the internal power supply. Use of the reverse power on/off sequences may result in the application of an overvoltage to the internal elements of the device, causing malfunction and degradation of internal elements due to the passage of an abnormal current. The correct power on/off sequence must be judged separately for each device and according to related specifications governing the device.
- (6) INPUT OF SIGNAL DURING POWER OFF STATE : Do not input signals or an I/O pull-up power supply while the device is not powered. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Input of signals during the power off state must be judged separately for each device and according to related specifications governing the device.